

ABSTRACT OF THE DISCLOSURE

In a liquid phase growth process comprising  
immersing a substrate in a melt held in a crucible, a  
crystal material having been dissolved in the melt, and  
5 growing a crystal on the substrate, at least a group of  
substrates to be immersed in the melt held in the  
crucible are fitted to the supporting rack at a  
position set aside from the center of rotation of the  
crucible or supporting rack, and the crystal is grown  
10 on the surface of the substrate thus disposed. This  
can provide a liquid phase growth process which can  
attain a high growth rate, can enjoy uniform  
distribution of growth rate in each substrate and  
between the substrates even when substrates are set in  
15 a large number in one batch, and can readily keep the  
melt from reaction and contamination even when the  
system has a large size, and provide a liquid phase  
growth system suited for carrying out the process.